

#### Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <a href="http://www.nxp.com">http://www.nxp.com</a>, <a href="http://www.semiconductors.philips.com/">http://www.nxp.com</a>, <a href="http://www.nexperia.com">http://www.nexperia.com</a>, <a href="http://www.nexperia.com">http://www.nexperia.com</a>)

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use salesaddresses@nexperia.com (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# PESD5V0U1BA; PESD5V0U1BB; PESD5V0U1BL

Ultra low capacitance bidirectional ESD protection diodes

Rev. 01 — 25 April 2007

Product data sheet

### **Product profile**

### 1.1 General description

Ultra low capacitance bidirectional ElectroStatic Discharge (ESD) protection diodes in small Surface-Mounted Device (SMD) plastic packages designed to protect one data line from the damage caused by ESD.

Table 1. **Product overview** 

Type number	Package		Package
	NXP	JEITA	configuration
PESD5V0U1BA	SOD323	SC-76	very small
PESD5V0U1BB	SOD523	SC-79	flat lead ultra small
PESD5V0U1BL	SOD882	-	leadless ultra small

#### 1.2 Features

- Bidirectional ESD protection of one line Ultra low leakage current: I<sub>RM</sub> = 5 nA
- Ultra low diode capacitance: C<sub>d</sub> = 2.9 pF ESD protection of up to 10 kV
- IEC 61000-4-2; level 4 (ESD)

### 1.3 Applications

- Computers and peripherals
- Audio and video equipment
- Cellular handsets and accessories
- 10/100/1000 Ethernet
- Local Area Network (LAN) equipment
- Communication systems
- Portable electronics
- Subscriber Identity Module (SIM) card protection
- FireWire
- High-speed data lines

#### 1.4 Quick reference data

Quick reference data

 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
$V_{RWM}$	reverse standoff voltage		-	-	5	V
$C_d$	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	2.9	3.5	pF



### Ultra low capacitance bidirectional ESD protection diodes

#### **Pinning information** 2.

Table 3. Pinning

Pin	Description	Simplified outline	e Symbol
SOD323; \$	SOD523		
1	cathode 1	<u>[1]</u>	
2	cathode 2	001aab540	1 2 sym045
SOD882			
1	cathode 1	<u>[1]</u>	
2	cathode 2	Transparent top view	1 2 sym045

<sup>[1]</sup> The marking bar indicates the cathode.

#### **Ordering information** 3.

**Ordering information** Table 4.

Type number	Package		
	Name	Description	Version
PESD5V0U1BA	SC-76	plastic surface-mounted package; 2 leads	SOD323
PESD5V0U1BB	SC-79	plastic surface-mounted package; 2 leads	SOD523
PESD5V0U1BL	-	leadless ultra small plastic package; 2 terminals; body $1.0\times0.6\times0.5$ mm	SOD882

### **Marking**

Table 5. Marking codes

3	
Type number	Marking code
PESD5V0U1BA	AA
PESD5V0U1BB	B3
PESD5V0U1BL	AN

PESD5V0U1BA\_BB\_BL\_1 Rev. 01 — 25 April 2007

**Product data sheet** 

2 of 12

### Ultra low capacitance bidirectional ESD protection diodes

### 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

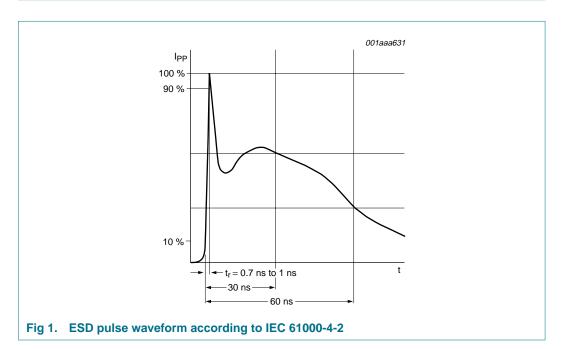
Table 7. ESD maximum ratings

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V <sub>ESD</sub> electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	[1][2]	-	10	kV	
		MIL-STD-883 (human body model)		-	8	kV

<sup>[1]</sup> Device stressed with ten non-repetitive ESD pulses.

Table 8. ESD standards compliance

Standard	Conditions
Per diode	
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3 (human body model)	> 4 kV



<sup>[2]</sup> Measured from pin 1 to pin 2.

### Ultra low capacitance bidirectional ESD protection diodes

#### **Characteristics** 6.

Table 9. **Characteristics** 

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
$V_{RWM}$	reverse standoff voltage		-	-	5	V
I <sub>RM</sub>	reverse leakage current	$V_{RWM} = 5 V$	-	5	100	nA
$V_{BR}$	breakdown voltage	$I_R = 5 \text{ mA}$	5.5	7	9.5	V
$C_d$	diode capacitance	f = 1 MHz				
		$V_R = 0 V$	-	2.9	3.5	pF
		$V_R = 5 V$	-	1.9	-	pF
r <sub>dif</sub>	differential resistance	$I_R = 1 \text{ mA}$	-	-	100	Ω

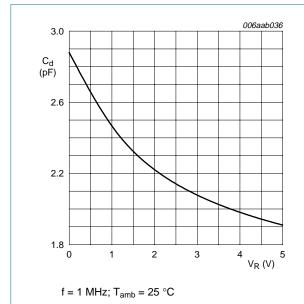


Fig 2. Diode capacitance as a function of reverse voltage; typical values

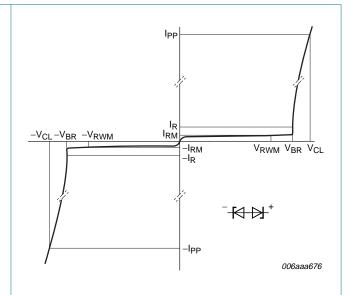
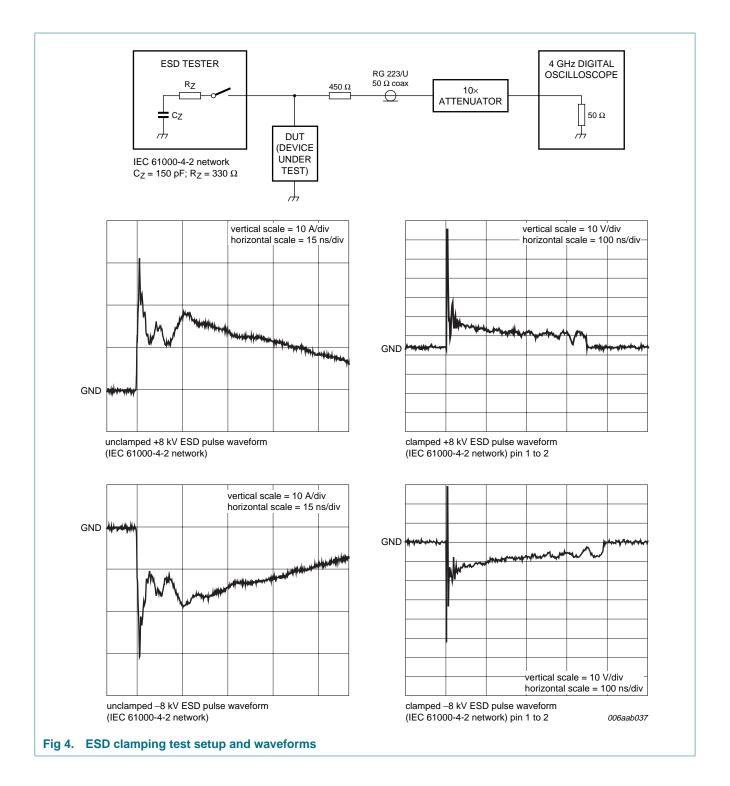


Fig 3. V-I characteristics for a bidirectional ESD protection diode

4 of 12

### Ultra low capacitance bidirectional ESD protection diodes

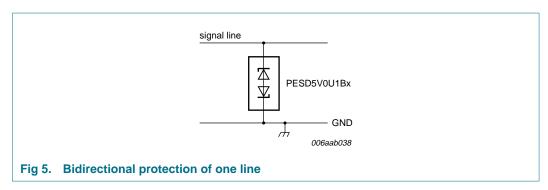


PESD5V0U1BA\_BB\_BL\_1 © NXP B.V. 2007. All rights reserved.

Ultra low capacitance bidirectional ESD protection diodes

#### **Application information** 7.

The PESD5V0U1Bx series is designed for the bidirectional protection of one signal line from the damage caused by ESD pulses. The PESD5V0U1Bx series may be used on lines where the signal polarities are either positive or negative with respect to ground.



#### Circuit board layout and protection device placement

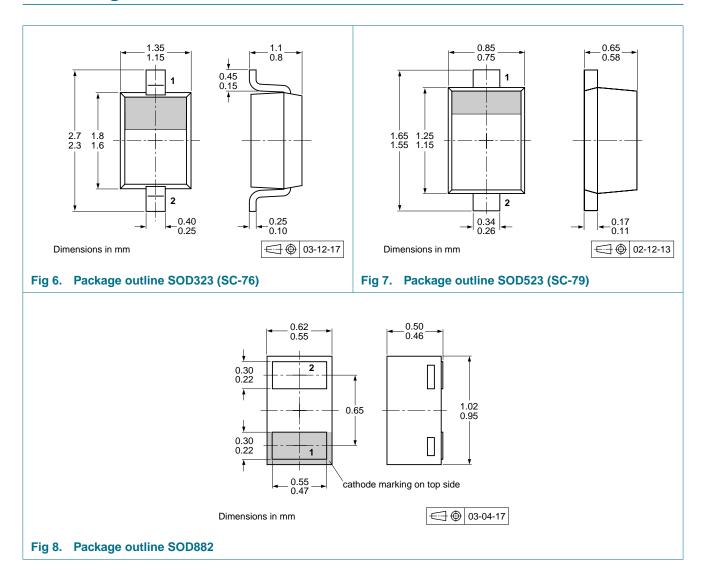
Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the PESD5V0U1Bx as close to the input terminal or connector as possible.
- 2. The path length between the PESD5V0U1Bx and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

6 of 12

Ultra low capacitance bidirectional ESD protection diodes

### Package outline



PESD5V0U1BA\_BB\_BL\_1 © NXP B.V. 2007. All rights reserved. Rev. 01 — 25 April 2007

7 of 12

#### Ultra low capacitance bidirectional ESD protection diodes

### 9. Packing information

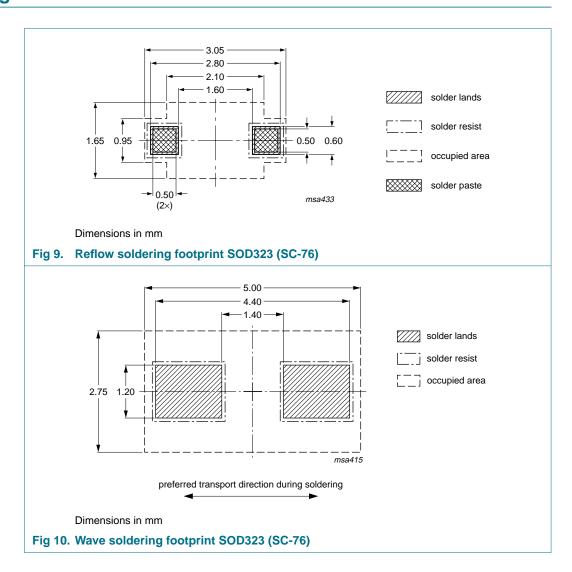
Table 10. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

		3			
Type number	Package	Description	Packin	g quanti	ty
			3000	8000	10000
PESD5V0U1BA	SOD323	4 mm pitch, 8 mm tape and reel	-115	-	-135
PESD5V0U1BB	SOD523	2 mm pitch, 8 mm tape and reel	-	-315	-
		4 mm pitch, 8 mm tape and reel	-115	-	-135
PESD5V0U1BL	SOD882	2 mm pitch, 8 mm tape and reel	-	-	-315

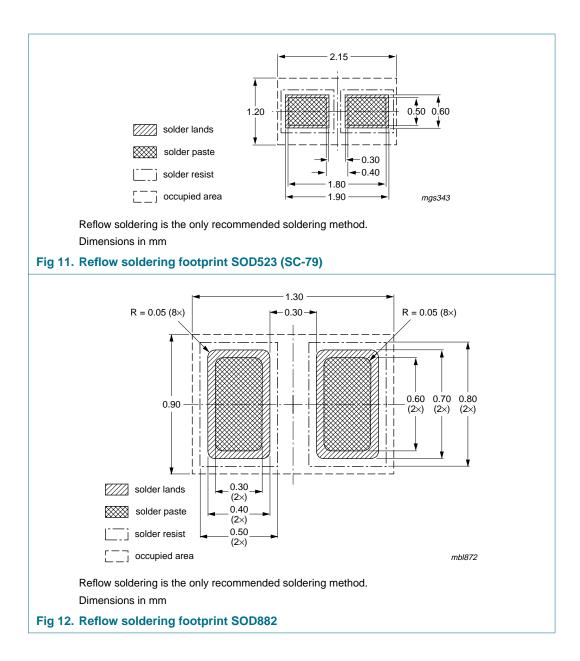
<sup>[1]</sup> For further information and the availability of packing methods, see Section 13.

### 10. Soldering



PESD5V0U1BA\_BB\_BL\_1 © NXP B.V. 2007. All rights reserved.

### Ultra low capacitance bidirectional ESD protection diodes



PESD5V0U1BA\_BB\_BL\_1 © NXP B.V. 2007. All rights reserved. Rev. 01 — 25 April 2007

9 of 12

Ultra low capacitance bidirectional ESD protection diodes

### 11. Revision history

#### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PESD5V0U1BA_BB_BL_1	20070425	Product data sheet	-	-

PESD5V0U1BA\_BB\_BL\_1 © NXP B.V. 2007. All rights reserved. Rev. 01 — 25 April 2007

10 of 12

#### Ultra low capacitance bidirectional ESD protection diodes

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

#### 12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

### 12.3 Disclaimers

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of a NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

#### 12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

#### 13. Contact information

For additional information, please visit: http://www.nxp.com

For sales office addresses, send an email to: <a href="mailto:salesaddresses@nxp.com">salesaddresses@nxp.com</a>

PESD5V0U1BA\_BB\_BL\_1 © NXP B.V. 2007. All rights reserved.

### Ultra low capacitance bidirectional ESD protection diodes

### 14. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
1.4	Quick reference data
2	Pinning information
3	Ordering information
4	Marking
5	Limiting values
6	Characteristics
7	Application information
8	Package outline
9	Packing information
10	Soldering
11	Revision history
12	Legal information1
12.1	Data sheet status
12.2	Definitions
12.3	Disclaimers
12.4	Trademarks1
13	Contact information
14	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



All rights reserved.



founded by

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 25 April 2007
Document identifier: PESD5V0U1BA\_BB\_BL\_1